

INCH-POUND

The documentation and process conversion measures necessary to comply with this document shall be completed by 5 September 2019.

MIL-PRF-19500/535G
5 June 2019
SUPERSEDING
MIL-PRF-19500/535F
3 March 2016

PERFORMANCE SPECIFICATION SHEET

TRANSISTOR, PNP, SILICON, POWER, TYPES 2N5003 AND 2N5005, ENCAPSULATED (CASE MOUNT PACKAGE) AND UNENCAPSULATED, QUALITY LEVELS JAN, JANTX, JANTXV, JANS, JANHC, AND JANKC

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

1.1 Scope. This specification covers the performance requirements for PNP, silicon, through hole power transistors for use in high-speed power-switching applications. Four levels of product assurance (JAN, JANTX, JANTXV, and JANS) are provided for each encapsulated device type and two levels of product assurance (JANHC and JANKC) are provided for unencapsulated devices as specified in [MIL-PRF-19500](#).

1.2 Physical dimensions.

1.2.1 Package outlines. The device package outline is a TO-210AA (formerly TO-59) in accordance with [figure 1](#) for all encapsulated device types.

1.2.2 Unencapsulated die. The dimensions and topography for JANHC and JANKC unencapsulated die are in accordance with [figure 2](#).

1.3 Maximum ratings unless otherwise specified $T_A = +25^\circ\text{C}$.

P_T (1) $T_A = 25^\circ\text{C}$	P_T (2) $T_C = 25^\circ\text{C}$	$R_{\theta JA}$	$R_{\theta JC}$ (3)	V_{CBO}	V_{CEO}	V_{EBO}	I_C	I_C (4)	Reverse pulse energy (5)	T_{stg} and T_J
<u>W</u>	<u>W</u>	<u>$^\circ\text{C/W}$</u>	<u>$^\circ\text{C/W}$</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>mJ</u>	<u>$^\circ\text{C}$</u>
2	58	88	3	-100	-80	-5.5	-5	-10	15	-65 to +200

- (1) Derate linearly 11.4 mW/ $^\circ\text{C}$ for $T_A > +25^\circ\text{C}$.
- (2) For derating see [figure 3](#).
- (3) For thermal impedance see [figure 4](#).
- (4) This value applies for $P_W \leq 8.3$ ms, duty cycle ≤ 1 percent.
- (5) This rating is based on the capability of the transistors to operate safely in the unclamped inductive load energy test circuit [figure 5](#) herein.

Comments, suggestions, or questions on this document should be addressed to DLA Land and Maritime, ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to Semiconductor@dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil>.

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